



Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP033X1/NVLS-000498X1	Application No.: 10/649,351
	Applicant: Lee et al.	
	Filing Date August 26, 2003	Group 1762

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1			/			

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B1			/				

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
lm	C1 1	Klaus et al., "Atomically Controlled Growth of Tungsten and Tungsten Nitride Using Sequential Surface Reactions," Applied Surface Science, 162-163, (2000) 479-491.
lm	C2 2	Li et al., "Deposition of W_Nx_Cy Thin Films by ALCVD TM Method for Diffusion Barriers in Metallization," IITC Conference Report, 2002, 3 Pages.
	C3 3	Elam et al, "Nucleation and Growth During Tungsten Atomic Layer Deposition on SiO_2 Surfaces," Thin Solid Films, 2001, 13 Pages.
	C4 4	Collins et al., "Pulsed Deposition of Ultra Thin Tungsten for Plugfill of High Aspect Ratio Contacts," Presentation made at Semicon Korea 2003, January 21, 2003, 9 pages.
	C5 5	Collins, et al., "Pulsed Deposition of Ultra Thin Tungsten for Plugfill of High Aspect Ratio Contacts," Semiconductor Equipment and Materials International, Semicon Korea, January 21, 2003, 3 pages.
	C6 6	Lee et al., "Pulsed Deposition of Ultra Thin Tungsten and its Application for Plugfill of High Aspect Ratio Contacts, Abstract, January 21, 2003, 1 page.
lm	Additional 21, 2003, 9 Pages	Collins et al., "Pulsed Deposition of Ultra Thin Tungsten for Plugfill of High Aspect Ratio Contacts," Presentation made at Semicon Korea 2003, January 21, 2003, 9 Pages
Examiner lm		Date Considered 2-3-5

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. NOVLP033X1/NVLS- 000498X1	Application No.: UNASSIGNED
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	Filing Date HEREWITH	Group UNASSIGNED

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
im	A1	6,143,082	11/07/00	McInerney et al.			
	A2	5,795,824	08/18/98	Hancock			
	A3	4,804,560	2/89	Shioya et al.			
	A4	5,661,080	08/97	Hwang et al.			
	A5	5,726,096	3/98	Jung			
	A6	5,804,249	9/98	Sukharev et al.			
	A7	6,294,468	09/01	Gould-Choquette et al.			
	A8	5,391,394	02/95	Hansen			
	A9	6,245,654	06/01	Shih et al.			
	A10	6,297,152	10/01	Itoh et al.			
	A11	6,265,312	07/01	Sidhwa et al.			
	A12	5,956,609	09/99	Lee et al.			
	A13	6,309,966	10/01	Govindarajan et al.			
	A14	5,250,329	10/93	Miracky et al.			
	A15	6,066,366	5/00	Berenbaum et al.			
	A16	5,817,576	10/98	Tseng et al.			
	A17	5,326,723	07/94	Petro et al.			
	A18	5,028,565	07/91	Chang et al.			

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
	B1						Yes	No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
im	C1	George et al., "Surface Chemistry for atomic Layer Growth", J. Phys. Chem, 1996, vol. 100, no, 31, pgs. 13121-13131.

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Filing Date	HEREWITH	UNASSIGNED

<i>Jim</i>	C2	Bell et al., "Batch Reactor Kinetic Studies of Tungsten LPCVD from Silane and Tungsten Hexafluoride", J. Electrochem. Soc., January 1996, Vol. 143, No. 1, pgs. 296-302.
<i>Jim</i>	C3	Klaus et al., "Atomically controlled growth of Tungsten and Tungsten nitride using sequential surface reactions", Applied Surface Science, 162-163 (2000) 479-491. ✓
<i>Jim</i>	C4	Klaus et al., "Atomic layer deposition of tungsten using sequential surface chemistry with a sacrificial stripping reaction", Thin Solid Films 360 (2000) 145-153.
Examiner <i>Jim</i>		Date Considered <i>2-3-5</i>

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